

●Electrical characteristics (Ta=25°C Unless otherwise specified)

	Item	Symbol	Conditions	Min.	Typ.	Max.	Unit	
Thyristor	Forward voltage drop	V _{FM}	T _j =25°C, I _{FM} =20A			1.40	V	
	Reverse current	I _R RM	T _j =125°C, V _R =V _R RM			4	mA	
	Off current	I _D RM	T _j =125°C, V _R =V _D RM			4	mA	
	Gate trigger current	I _{GT}	T _j =25°C, V _D =6V I _T =1A			80	mA	
	Gate trigger voltage	V _{GT}				2.5	V	
	Gate non-trigger voltage	V _{GD}	T _j =125°C, V _D =1/2V _D RM	0.2			V	
		I _H				150	mA	
		dv/dt	T _j =125°C, V _D =2/3V _D RM	500			V/μs	
		Turn-on time	t _{gt}	T _j =25°C, V _D =1/2V _D RM I _{TM} =40A I _{GM} =0.3A diG/dt=0.3A/μs		3		μs
		Turn-off time	T _q	T _j =125°C, I _{TM} =20A -di/dt=5A/μs V _R >=50v V _D =1/2V _D RM		100		μs
Diode	Forward voltage drop	V _{FM}	T _j =25°C, I _{FM} =20A			1.20	V	
	Reverse current	I _R RM	T _j =125°C, V _R =V _R RM			3	mA	

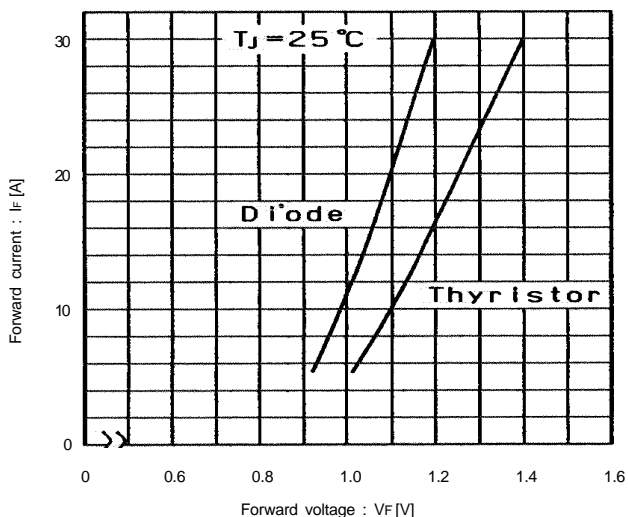
● Thermal Characteristics

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Thermal resistance	R _{th(j-c)}	Junction to case Thyristor			2.5	°C/W
		1 Chip Diode			3.0	
	R _{th(c-f)}	the base to cooling fin *			0.06	°C/W

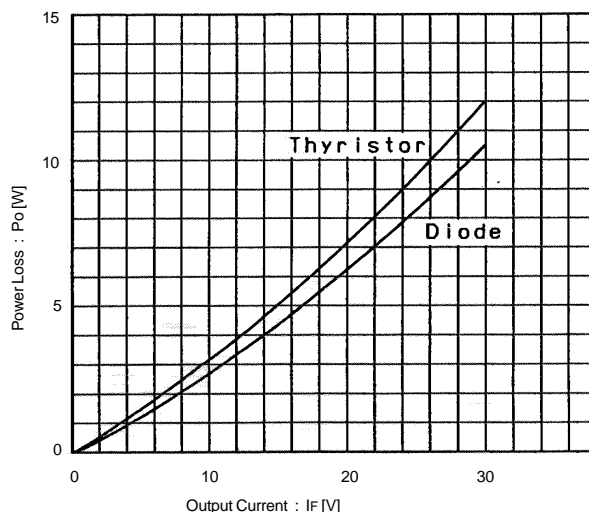
*:Screw torque 2.5N·m, With Thermal Compound

■ Characteristics

Maximum On-State Voltage/Forward Voltage Characteristics (Per 1 chip)

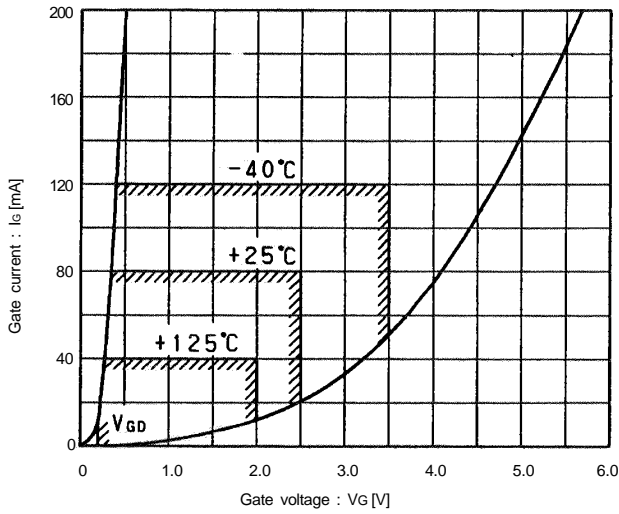


Output Current vs. Power Loss (Per 1 chip)

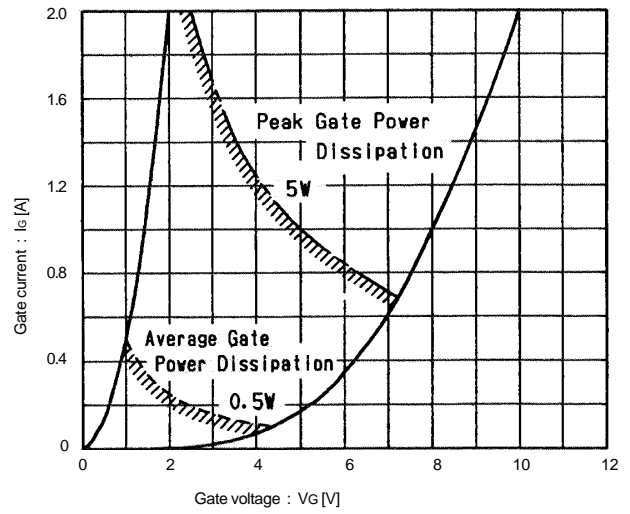


■ Characteristics

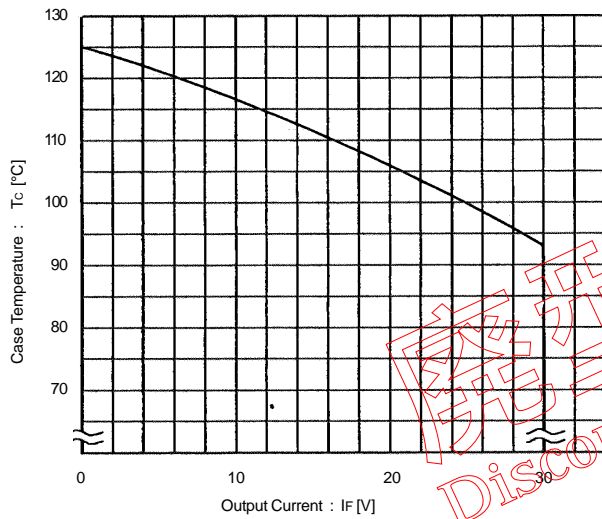
Gate Characteristics



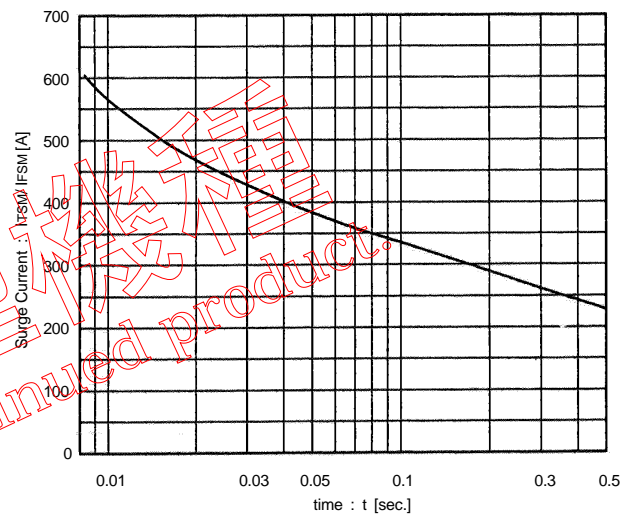
Gate Characteristics



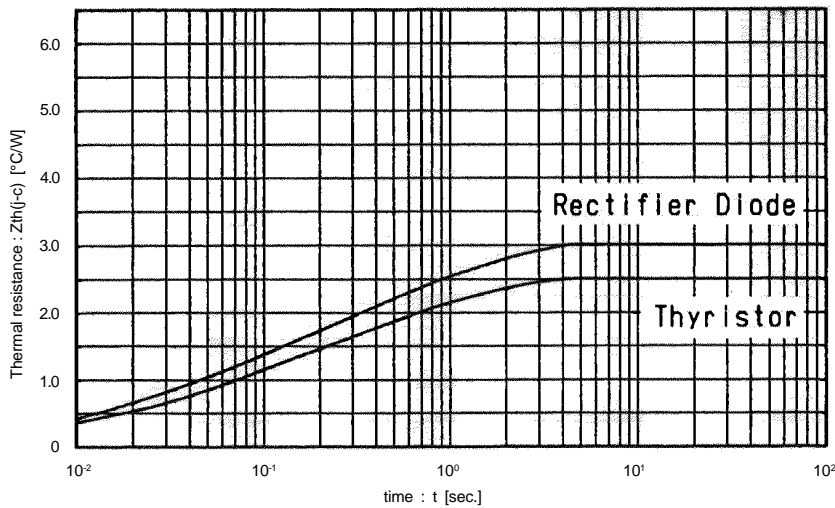
Output Current vs. Case Temperature



Surge Current



Transient Thermal Impedance
(Per 1 chip, Junction to Case)



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 諸君 留意
 Discontinued product.